

# ONFI 4.0: Faster I/O speeds at lower power consumption

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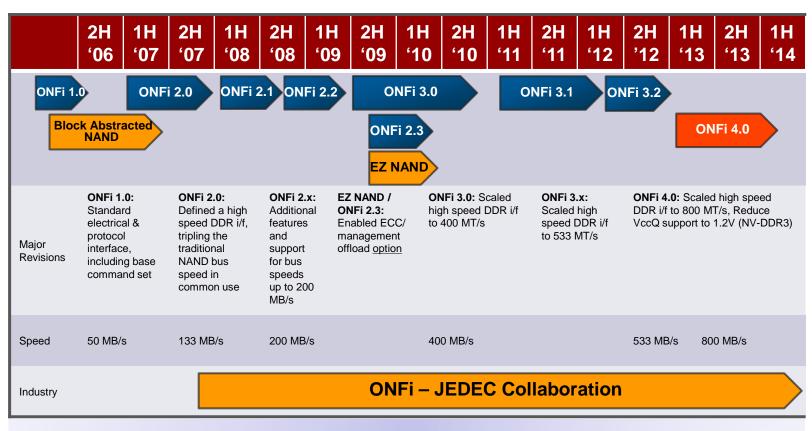


## emory ONFI 4.0: Adopted April 2014

- Reduces I/O power consumption
  - Lower I/O voltage
  - Reduced termination requirements
- Increases I/O performance
  - Scale I/O speeds faster as NAND page sizes grow
  - Soft data requirements
  - Latency reduction
- Continues interoperability between vendors
  - Collaboration in JC42.4 ONFI/JEDEC Joint Task Group



## ONFI Workgroup Continues To Produce Results!



ONFI has and continues to deliver innovation & interoperability enabling faster NAND adoption



#### Memory ONFI 4.0 Features

- NV-DDR3:
  - VccQ = 1.2V (1.14V 1.26V)
  - Evolutionary interface from NV-DDR2
    - Same packaging, Opcodes, timing diagrams/parameters, etc
    - All of the ONFI 3.x features will continue to be supported
      - Matrix Termination, CE reduction, Volume addressing,
         Differential signaling, VPP, External VrefQ, Warm Up cycles,
         etc...
    - Same output drive strength and RTT settings
- Maximum I/O speeds increased
  - 667 MT/s and 800 MT/s timing modes added
- ZQ calibration supported
  - RZQ = 300 ohms +/- 1%
  - Long (F9h) and Short (D9h) Calibration commands



#### nory ONFI 4.0 Differences

- Devices that support NV-DDR3 may not support VccQ = 3.3V
- NV-DDR3 Interface will not power up in SDR (i.e. Async)
  - SDR, NV-DDR, NV-DDR2 not supported at VccQ=1.2V
  - Agnostic READ ID will provide information on power on interface
- tADL and tCCS will push out due to larger page sizes and data path design requirements to achieve faster I/O speeds
- Electrical Package Specifications for Zpk and Tpd
  - Same methodology as DRAM DDR4
- Possible reduced Driver strength settings supported

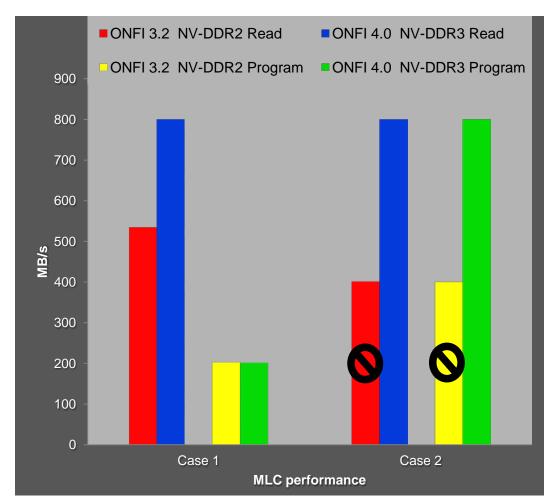


#### Memory ONFI 4.0 Performance

- Numbers are highly dependent on NAND/system architecture
  - Page size / number of LUNs
  - Number of planes
  - tPROG/tR
  - Programming Algo
  - Available System buffering
- SI highly dependent on a number of factors
  - Topology
  - Channel length
  - Package Zpk/Tpd
  - PCB Design

Santa Clara, CA

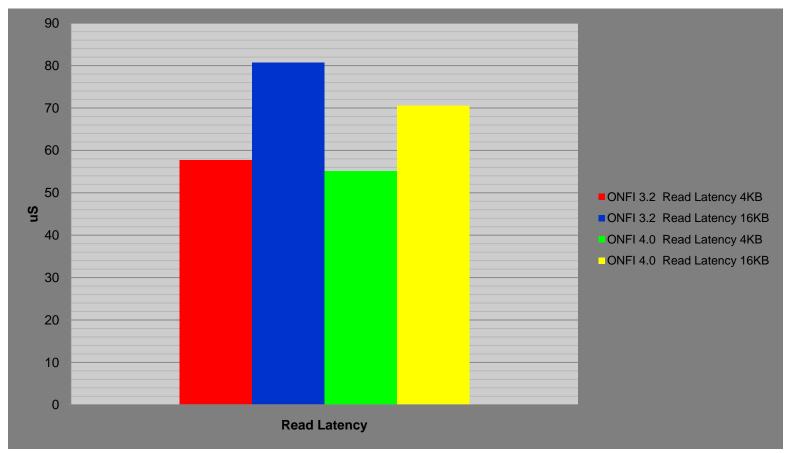
- Impedance
- Trace matching
- Available drive strengths/RTT
- RON/RTT variance
- Controller overshoot restrictions
- Controller/NAND capacitance



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## Flash Memory Read Latency



4KB read latency has diminishing returns

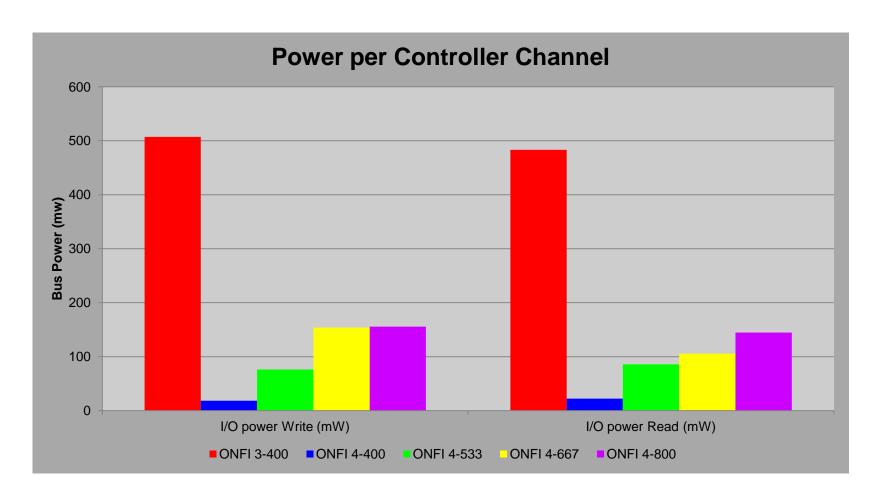


#### Memory ONFI 4.0 Bus Power Reduction

- Switching power reduction
  - P = FV<sup>2</sup>C V: 1.8V -> 1.2V C: Significantly Reduced
- Termination power reduction
  - Rtt requirements reduced
- NAND data path power reduction
  - Can provide improved NAND data path power biasing



## Memory Power comparisons

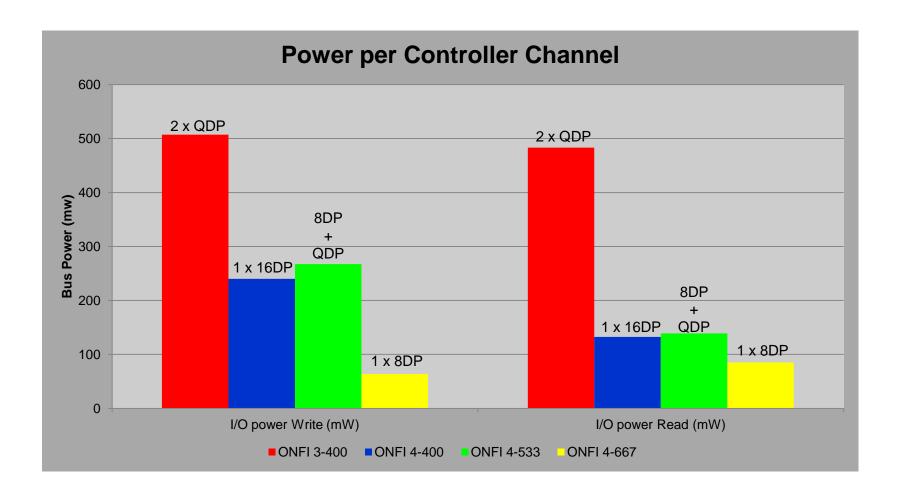


- Reduced Die Capacitance and smaller signaling also enables new topologies and increased fan-out:
  - 8 Die per channel at 400 MT/s with no termination
  - 16 Die per channel at 533 MT/s
  - 12 Die per channel at 667 MT/s
  - 8 Die per channel at 800 MT/s

Estimates are based on Signal Integrity analysis, actual performance may vary based on a number of system variables



### Memory More LUNs per channel





- ONFI 4.0 provides:
  - I/O Performance improvements
  - I/O and NAND Power consumption improvements
  - Straightforward evolutionary enablement
  - Industry interoperability
- ONFI 4.0 specification available for download
  - www.onfi.org/specifications